XP-002191010

AN - 1975-29790W [18]

CPY - NARU

DC - L02 L03 U12

FS - CPI;EPI

IC - C04B0/00; H01L0/00

MC - L02-G03A L03-D03G

PA - (NARU) NARUTSU SEITO KK

PN - JP50008442B B 19750404 DW197518 000pp

PR - JP19680067060 19680916

XIC - C04B-000/00; H01L-000/00

AB - J75008442 A porcelain for sealing a semi-conductor, comprises periclase, barium magnesium silicate and forsterite, and is produced by adding 3-10 wt.% of a mineraliser to 100 wt.% of a MgO-BaO-SiO2 type compsn. which is included in a polygonal area constructed by drawing in succession lines between the point A(MgO:49.4; BaO:10.0; SiO2:40.6) and the spot B(MgO:37.5, Ba0:25.0, SiO2:37.5) be between the spot B and the spot C(MgO:55.4; BaO;25.0; SiO2:19.6) between the spot C and the spot D(MgO:71.3, BaO:16.1, SiO2:12.6), and between the spot D and the spot E (MgO:76.5, BaO:10.0, SiO2:13.5), in the MgO-BaO-SiO2 type triangular diagram, (all quantities given in wt.%).

IW - PORCELAIN SEAL SEMICONDUCTOR COMPRISE PERICLASE BARIUM MAGNESIUM SILICATE FORSTERITE

IKW - PORCELAIN SEAL SEMICONDUCTOR COMPRISE PERICLASE BARIUM MAGNESIUM SILICATE FORSTERITE

NC - 001

OPD - 1968-09-16

ORD - 1975-04-04

PAW - (NARU) NARUTSU SEITO KK

TI - Porcelain for sealing semiconductors - comprises periclase, barium magnesium silicate and forsterite